

UNISONIC TECHNOLOGIES CO., LTD

TF5123

N-CHANNEL JUNCTION FIELD EFFECT TRANSISTOR

■ DESCRIPTION

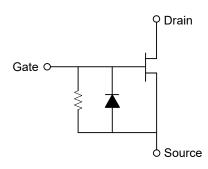
The UTC **TF5123** is an N-Channel Junction FET, it uses UTC's advanced technology to provide the customers with high voltage gain, etc.

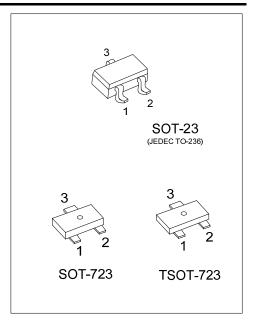
The UTC ${\ensuremath{\mathsf{TF5123}}}$ is suitable for electret capacitor microphone applications.

■ FEATURES

- * High voltage gain
- * For electret capacitor microphone

■ EQUIVALENT CIRCUIT

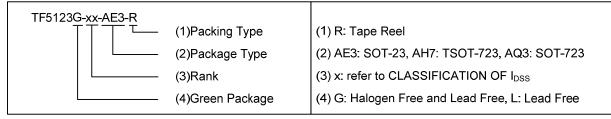




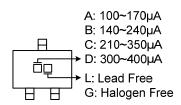
■ ORDERING INFORMATION

Ordering Number		Dealcana	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
TF5123L-xx-AE3-R	TF5123G-xx-AE3-R	SOT-23	D	S	G	Tape Reel	
TF5123L-xx-AH7-R	TF5123G-xx-AH7-R	TSOT-723	D	S	G	Tape Reel	
TF5123L-xx-AQ3-R	TF5123G-xx-AQ3-R	SOT-723	D	S	G	Tape Reel	

Note: Pin Assignment: D: Drain S: Source G: Gate



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Gate to Drain Voltage	V_{GDO}	-20	V
Drain Current	I _D	10	mA
Gate Current	I _G	10	mA
Allowable Power Dissipation	P _D	100	mW
Junction Temperature	TJ	+125	°C
Storage Temperature Range	T _{STG}	-55 ~ +125	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Gate to Drain Breakdown Voltage	$V_{(BR)GDO}$	I _G =-100μA	-20			V
Drain Current	I _{DSS}	V _{DS} =2V, V _{GS} =0V	100		400	μΑ
Gate Off Voltage	$V_{GS(OFF)}$	V _{DS} =2V, I _D =1μA, I _{DSS} =250μA		-0.3		V
Forward Transfer Admittance	Yfs	V _{DS} =2V, V _{GS} =0V, I _{DSS} =250µA		2.1		mS
Input Capacitance	Ciss	V _{DS} =2V, V _{GS} =0V, f=1MHz		9.0		pF
Voltage Gain	Gv	V_{DD} =2V, R _L =2.2k Ω , Cg=5pF, f=1kHz, V_{IN} =10mV, I_{DSS} =100 μ A		1.3		dB
		V_{DD} =2V, R _L =2.2k Ω , Cg=5pF, f=1kHz, V_{IN} =10mV, I _{DSS} =250 μ A		3.4		dB
		V_{DD} =2V, R _L =2.2k Ω , Cg=5pF, f=1kHz, V_{IN} =10mV, I _{DSS} =350 μ A		3.6		dB
Delta Voltage Gain	△G _V (V)	V_{DD} =2V~1.5V, R _L =2.2k Ω , Cg=5pF, f=1kHz, V_{IN} =10mV		-0.7		dB
Frequency Characteristics	△G _V (f)	V _{DD} =2V, R _L =2.2kΩ, Cg=5pF, f=1kHz~110Hz, V _{IN} =10mV		-0.2		dB
Output Noise Voltage	Vno	V_{DD} =3V, Cg=5pF, A-Curve Filter, R _L =1.0k Ω I_{DSS} =250 μ A		-107		dB
		V_{DD} =3V, Cg=5pF, A-Curve Filter, R _L =2.2k Ω I_{DSS} =250 μ A		-104		dB
Total Harmonic Distortion	THD	V_{DD} =2V, R _L =2.2k Ω , Cg=5pF, f=1kHz, V_{IN} =30mV, I_{DSS} =250 μ A		1.0		%

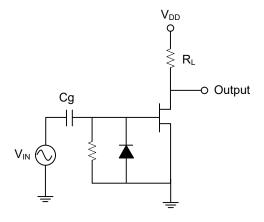
■ CLASSIFICATION OF I_{DSS}

RANK	Α	В	С	D
I _{DSS} (µA)	100 ~ 170	140 ~ 240	210 ~ 350	300 ~400

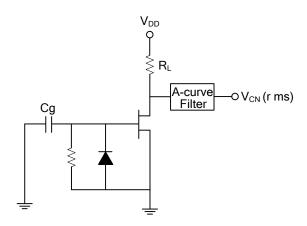
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■ TEST CIRCUITS

Voltage Gain Frequency Characteristics Total Harmonic Distortion

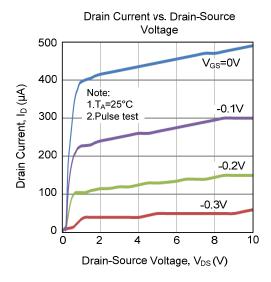


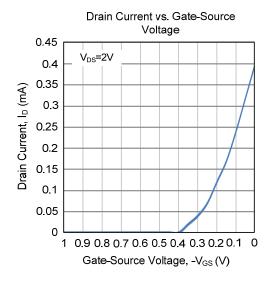
Output Noise Voltage

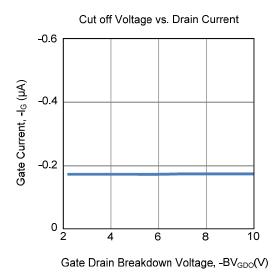


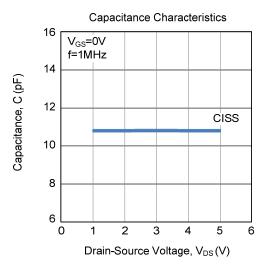
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■ TYPICAL CHARACTERISTICS









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